

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	2	"6183067".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/02/01 13:30
L5	1495	347/56	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/02/01 13:30
S1	2	"20050231557"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 09:27
S2	7	("2002046266" "0405204" "0456872").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:36
S3	27	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:07
S4	288	"347"/\$3 and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:35
S5	176	"347"/\$3 and micro\$fluid\$2 and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:36
S6	55	"347"/\$3 and micro\$fluid\$2 and silicon and (di\$electric\$2 or bi\$electric\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:43

S7	55	"347"/\$3 and micro\$fluid\$2 and silicon and (di\$electric\$2 or bi\$electric\$2) and (angstrom\$1 or A)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:41
S8	103	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:49
S9	58	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:50
S10	24	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 13:51
S11	3	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2 and (pitting or pitted)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:06
S12	3	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2 and angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:02
S13	24	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2 and A	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:25
S14	0	("6179401" "6637866" "5850242" "20040113988").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:08

S15	8	("6179401" "6637866" "5850242" "20040113988").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/30 15:08
S16	11417	(Krawczyk.in. or McNees.in. or Mrvos.in. or Sullivan.in.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:17
S17	110	(Krawczyk.in. or McNees.in. or Mrvos.in. or Sullivan.in.) and Lexmark	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:17
S18	9	(Krawczyk.in. or McNees.in. or Mrvos.in. or Sullivan.in.) and Lexmark and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/30 15:17
S20	24	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and ion and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:23
S21	0	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and micro\$fluid\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 07:52
S22	47	"347"/\$3 and di\$electric\$2 with angstrom\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:02
S23	3	"347"/\$3 and di\$electric\$2 with angstrom\$1 and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:16

S24	33	"347"/\$3 and micro\$fluid\$2 and silicon same (path\$1 or pathway\$1 or channel\$1 or trench\$2 or opening\$1) and (ion or etch\$3) and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 08:25
S25	0	TW0405204B	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:36
S26	394544	TW 0405204B	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:36
S27	0	TW and 0405204B	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:37
S28	0	TW and "0405204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:37
S29	0	TW and "00405204"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:37
S30	46	CHEN.in. and WU.in. and LUR.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:40
S31	0	CHEN.in. and WU.in. and LUR.in. and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:40

S32	27	CHEN.in. and WU.in. and LUR.in. and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:40
S33	10	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:41
S34	10	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:49
S35	1554385	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 adn oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:49
S36	8	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 09:42
S37	0	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide and root same mean same square	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:51
S38	123667	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide (pit or pitting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:52
S39	0	CHEN.in. and WU.in. and LUR.in. and silicon and di\$electric\$2 and etch\$3 and oxide and (pit or pitting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 08:52

S40	21	CHEN.in. and WU.in. and LUR.in. and silicon and etch\$3 and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 09:48
S41	3	CHEN.in. and WU.in. and LUR.in. and silicon and etch\$3 and oxide and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:02
S42	3	CHEN.in. and WU.in. and LUR.in. and silicon and etch\$3 and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:02
S43	1775	micro\$fluid\$2 and silicon and etch\$3 and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:03
S44	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:08
S45	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:08
S46	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon and (etch\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:10
S47	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon and (etch\$3) and oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:10

S48	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon and (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:15
S49	6	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate and (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:20
S50	5	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate same (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:26
S51	7	("3958255" "5087591" "5320932" "5350491" "5350492" "5362356" "6204182" "6207491" "6284606" "6294474" "6402301" "6595627" "6620732" "20010077163").pn. and (angstrom\$1 or nanometer\$1 or nm) and silicon with (etch\$3) and oxide and (thick\$4 or depth)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:16
S52	98	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and root near1 mean near1 square	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:39
S53	26	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) same root near1 mean near1 square	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:38
S54	1	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) same root near1 mean near1 square and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:39

S55	1	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and root near1 mean near1 square and microfluid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:39
S56	4	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and root near1 mean near1 square and microfluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:40
S57	254	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and microfluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:42
S58	44	(angstrom\$1 or nanometer\$1 or nm) and silicon near3 substrate with (etch\$3) and oxide and (thick\$4 or depth) and microfluid\$2 and inkjet\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 10:42
S59	6	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) with (root near1 mean near1 square) and (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:27
S60	5	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) with (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:43
S61	207	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1 or uneven or surface) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:47
S62	19	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:08

S63	24	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1 or uneven or pore\$1 or porous) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 12:48
S64	2	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and depth same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:09
S65	12	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and (depth or deep or thick or thickness) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:22
S66	12	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and (depth or deep or thick or thickness or holes or hole) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:30
S67	13	ion with etch\$3 and (pit\$4 or hole\$1 or cavity or cavities or path\$1 or channel\$1) same (root near1 mean near1 square) same (angstrom\$1 or nanometer\$1 or nm) and (pitting or pitted or pits or pit or depth or deep or thick or thickness or holes or hole) same (angstrom\$1 or nanometer\$1 or nm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:32
S68	1	S67 not S66	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/31 14:32
S69	1	ink\$jet\$4 with silicon and di\$electric and micro\$fluid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 15:12

S70	23	ink\$jet\$4 with silicon and (path\$1 or channel\$1) and micro\$fluid\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2006/01/31 15:13
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